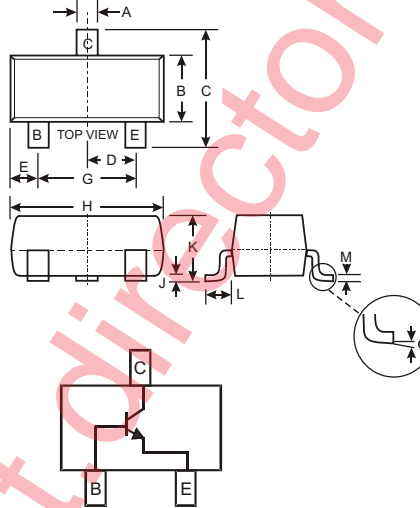


### Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT5401)
- Ideal for Medium Power Amplification and Switching
- Available in Lead Free/RoHS Compliant Version (Note 2)

### Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 5, on Page 2
- Marking (See Page 2): K4N
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approximate)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
$\alpha$	0°	8°
All Dimensions in mm		

### Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	MMBT5551	Unit
Collector-Base Voltage	V <sub>CB0</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EB0</sub>	6.0	V
Collector Current - Continuous (Note 1)	I <sub>C</sub>	200	mA
Power Dissipation (Note 1)	P <sub>d</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>θJA</sub>	417	°C/W
Operating and Storage and Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.  
2. No purposefully added lead.

## Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

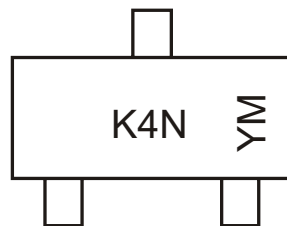
Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 3)</b>					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	180	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	160	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CBO}$	—	50	nA $\mu\text{A}$	$V_{CB} = 120\text{V}, I_E = 0$ $V_{CB} = 120\text{V}, I_E = 0, T_A = 100^\circ\text{C}$
Emitter Cutoff Current	$I_{EBO}$	—	50	nA	$V_{EB} = 4.0\text{V}, I_C = 0$
<b>ON CHARACTERISTICS (Note 3)</b>					
DC Current Gain	$h_{FE}$	80 80 30	— 250 —	—	$I_C = 1.0\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.15 0.20	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	1.0	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	$C_{obo}$	—	6.0	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Small Signal Current Gain	$h_{fe}$	50	250	—	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}, f = 1.0\text{kHz}$
Current Gain-Bandwidth Product	$f_T$	100	300	MHz	$V_{CE} = 10\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Noise Figure	nF	—	8.0	dB	$V_{CE} = 5.0\text{V}, I_C = 200\mu\text{A}, R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$

## Ordering Information (Note 4)

Device	Packaging	Shipping
MMBT5551-7	SOT-23	3000/Tape & Reel

- Notes: 3. Short duration test pulse used to minimize self-heating effect.  
 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.  
 5. For Lead Free/RoHS Compliant version part number, please add "-F" suffix to the part number above. Example: MMBT5551-7-F.

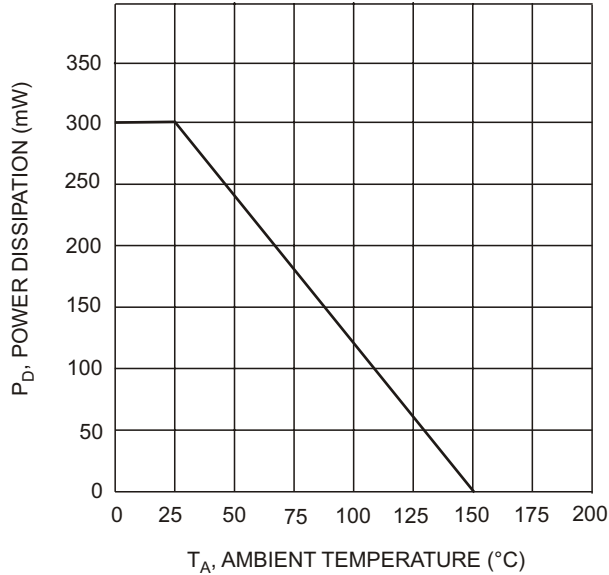
## Marking Information



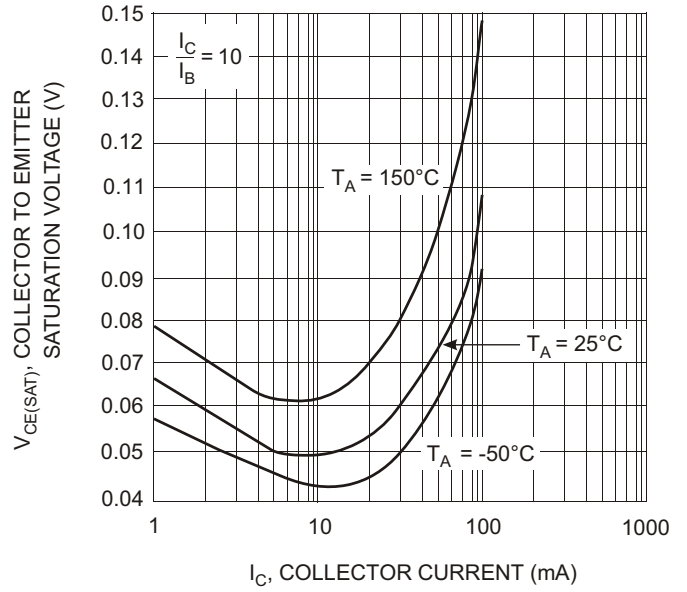
K4N = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

Date Code Key

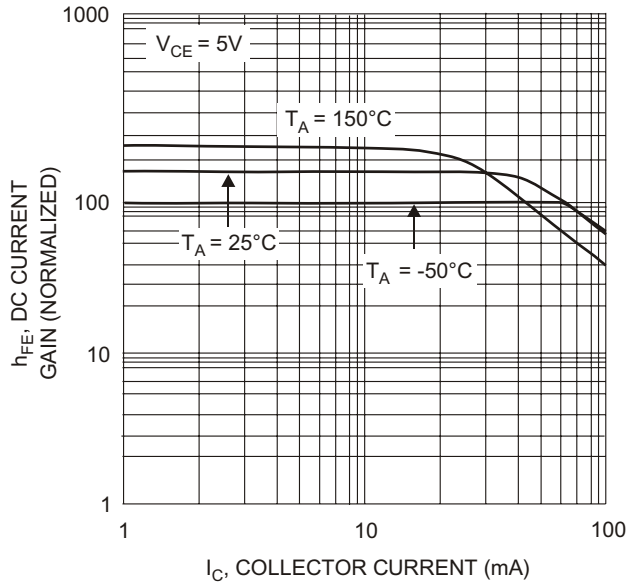
<b>Year</b>	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
<b>Code</b>	J	K	L	M	N	P	R	S	T	U	V	W
<b>Month</b>	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
<b>Code</b>	1	2	3	4	5	6	7	8	9	O	N	D



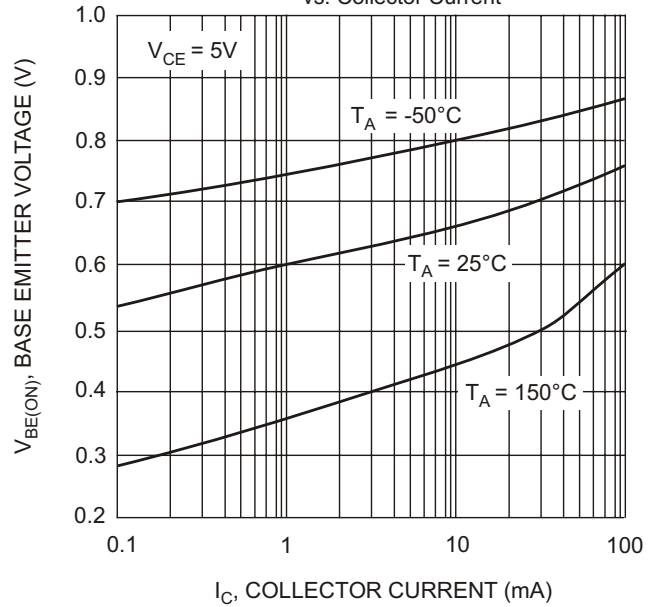
$T_A$ , AMBIENT TEMPERATURE (°C)  
Fig. 1, Max Power Dissipation vs Ambient Temperature



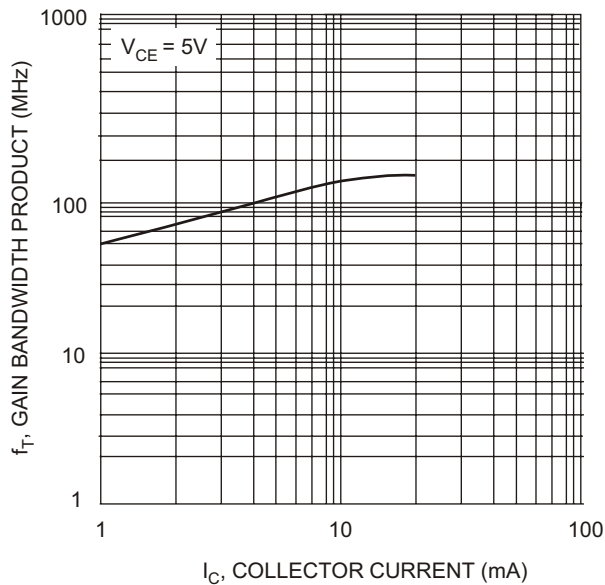
$I_C$ , COLLECTOR CURRENT (mA)  
Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current



$I_C$ , COLLECTOR CURRENT (mA)  
Fig. 3, DC Current Gain vs Collector Current



$I_C$ , COLLECTOR CURRENT (mA)  
Fig. 4, Base Emitter Voltage vs. Collector Current



$I_C$ , COLLECTOR CURRENT (mA)  
Fig. 5, Gain Bandwidth Product vs. Collector Current